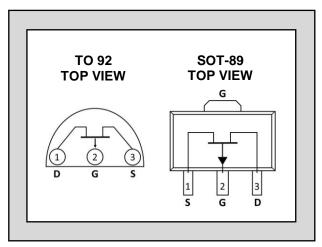


Twenty-Five Years Of Quality Through Innovation

LSJ74, SST74

ULTRA LOW NOISE SINGLE P-CHANNEL JFET

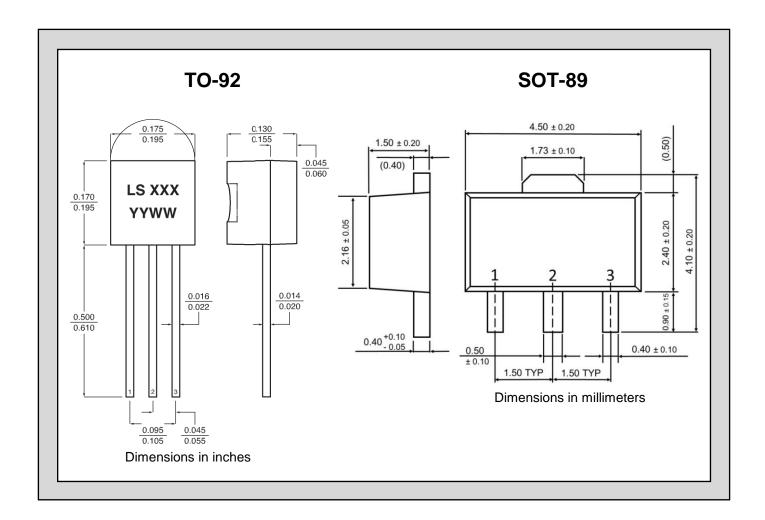
| FEATURES | | | | | |
|---|--|--|--|--|--|
| ULTRA LOW NOISE (f = 1kHz) | $e_n = 0.9 \text{nV}/\sqrt{\text{Hz}}$ | | | | |
| HIGH GAIN | $G_{fs} = 22mS (typ)$ | | | | |
| HIGH INPUT IMPEDANCE | $I_G = 1.0 \text{nA}$ | | | | |
| LOW CAPACITANCE | C _{RSS} = 32pF | | | | |
| IMPROVED SECOND SOURCE REPLACEMENT FOR 2SJ74 | | | | | |
| ABSOLUTE MAXIMUM RATINGS¹ @ 25 °C (unless otherwise stated) | | | | | |
| Maximum Temperatures | | | | | |
| Storage Temperature | -55 to +150°C | | | | |
| Junction Operating Temperature | -55 to +135°C | | | | |
| Maximum Power Dissipation | | | | | |
| Continuous Power Dissipation | 400mW | | | | |
| Maximum Currents | | | | | |
| Gate Forward Current | $I_{G(F)} = -10mA$ | | | | |
| Maximum Voltages | | | | | |
| Gate to Drain Voltage | $V_{GDS} = 25V$ | | | | |
| Gate to Source Voltage | V _{GSS} = 25V | | | | |



^{*} For equivalent N-Channel, see LSK170 family.

ELECTRICAL CHARACTERISTICS @ 25°C (unless otherwise stated)

| SYMBOL | CHARACTERISTIC | | MIN | TYP | MAX | UNITS | CONDITIONS | | |
|----------------------|--|--------|---------------|-----|------|-----------|--|--------|---|
| BV _{GDS} | Gate to Drain Breakdown Voltage | | 25 | | | V | $V_{DS} = 0V, I_G = 100 \mu A$ | | |
| V _{GS(OFF)} | Gate to Source Pinch-off Voltage | | 0.15 | | 2 | | $V_{DS} = -10V, I_{D} = -0.1 \mu A$ | | |
| Ibss | Drain to Source Saturation Current ² | LSJ74A | -2.6 | | -6.5 | mA | mA V _{DG} = -10V, V _{GS} = 0V | | |
| | | LSJ74B | -6 | | -12 | | | | |
| | | LSJ74C | -10 | | -20 | | | | |
| | | LSJ74D | -17 | | -30 | | | | |
| lg | Gate Operating Current | | | 50 | | pА | $V_{DG} = -10V, I_{D} = -1mA$ | | |
| Igss | Gate to Source Leakage Current | | | | 1 | nA | $V_{GS} = 25V$, $V_{DS} = 0V$ | | |
| G _{fss} | Full Conductance Transconductance | | 8 | 22 | | mS | $V_{DG} = -10V$, $V_{GS} = 0V$, $f = 1kHz$ | | |
| | Noise Voltage | | Naisa Valtaga | | | 0.9 | 1.9 | nV/√Hz | $V_{DS} = -10V$, $I_D = -2mA$, $f = 1kHz$, $NBW = 1Hz$ |
| e n | | | | 2.5 | 4 | IIV/ VIIZ | $V_{DS} = -10V$, $I_{D} = -2mA$, $f = 10kHz$, $NBW = 1Hz$ | | |
| C _{ISS} | Common Source Input Capacitance | | | 105 | · | pF | $V_{DS} = -10V$, $V_{GS} = 0V$, $f = 1MHz$ | | |
| Crss | Common Source Reverse Transfer Cap. | | | 32 | | | $V_{DS} = -10V, I_D = 0A, f = 1MHz$ | | |



NOTES:

- 1. Absolute maximum ratings are limiting values above which serviceability may be impaired.
- 2. Pulse test: PW \leq 300 μ S, Duty Cycle \leq 3%.
- 3. All MIN/TYP/MAX Limits are absolute values. Negative signs indicate negative electrical polarity only.

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